

# LVDS-type On-Chip Transmission Line Interconnect with Passive Equalizers in 90 nm CMOS Process

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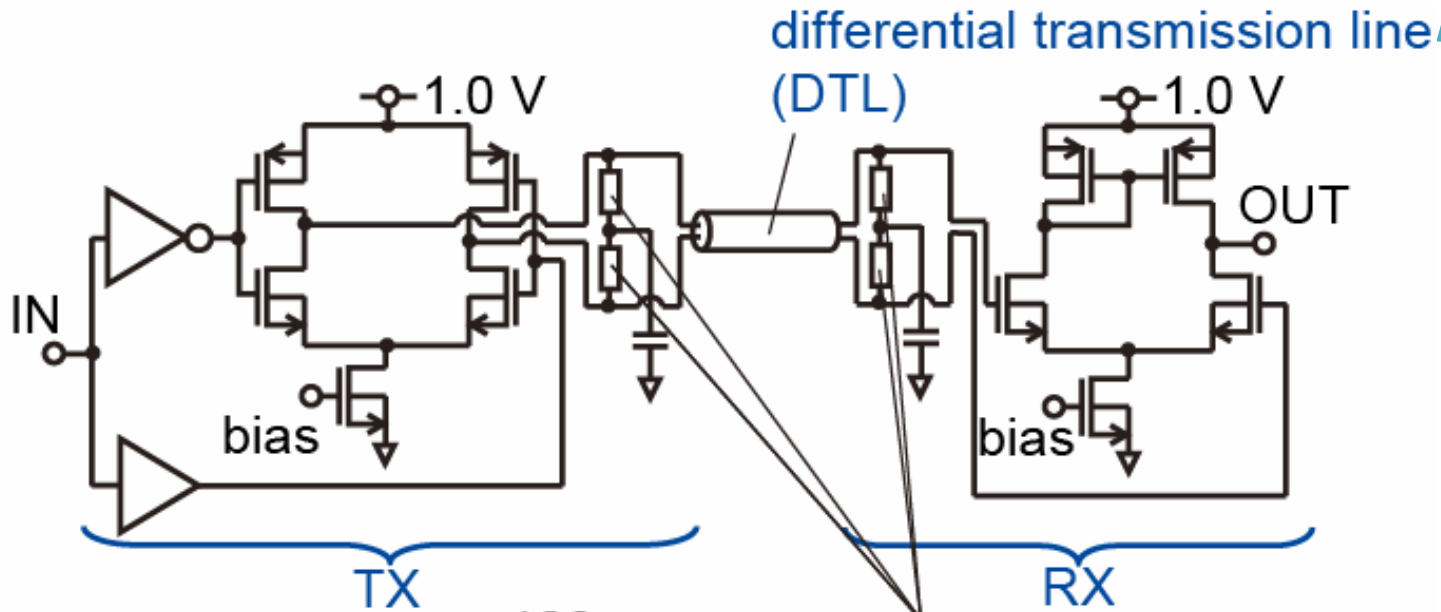
- Miniaturization of Si CMOS
  - Increase in global interconnect delays
    - Complicates timing designs
    - Limits LSI performances
- Transmission line interconnects<sup>[1]</sup>
  - Much smaller delay than conventional lines
  - High power-efficiencies at high-speed signaling

## Purpose

To propose a low-voltage-differential-signaling (LVDS) type transmission line interconnect for achieving higher speed and higher power-efficiency

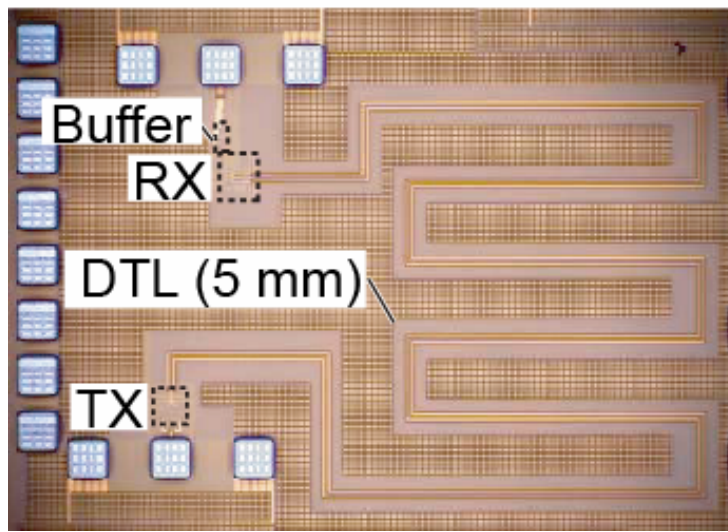
[1]R. T. Chang, *et al.*, IEEE JSSC, vol. 38, no. 5, pp. 834-838, May 2003.

# The proposed DTL interconnect

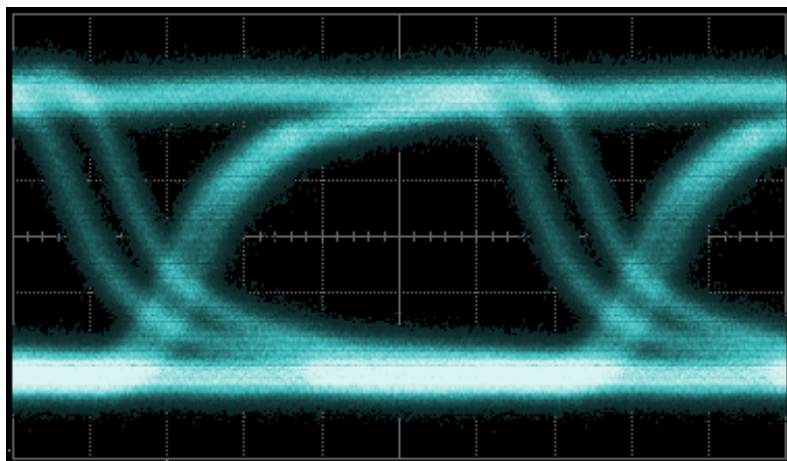


100  $\mu\text{m}$

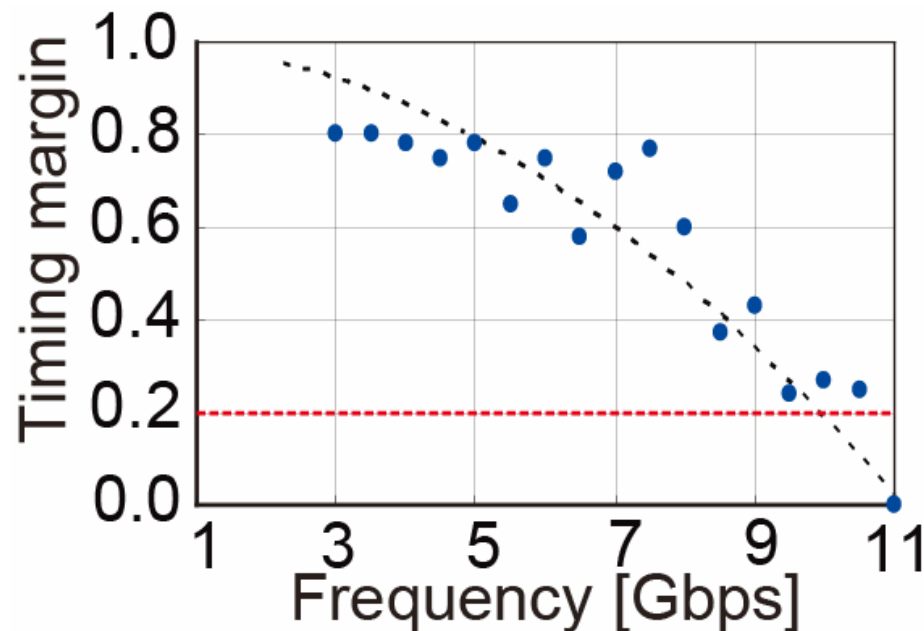
small-area inductor  
(passive equalization)  
10.0  $\mu\text{m}$  x 12.8  $\mu\text{m}$   
0.5 nH, Q = 2



90 nm CMOS process  
Total area of TX and RX is 11,100  $\mu\text{m}^2$



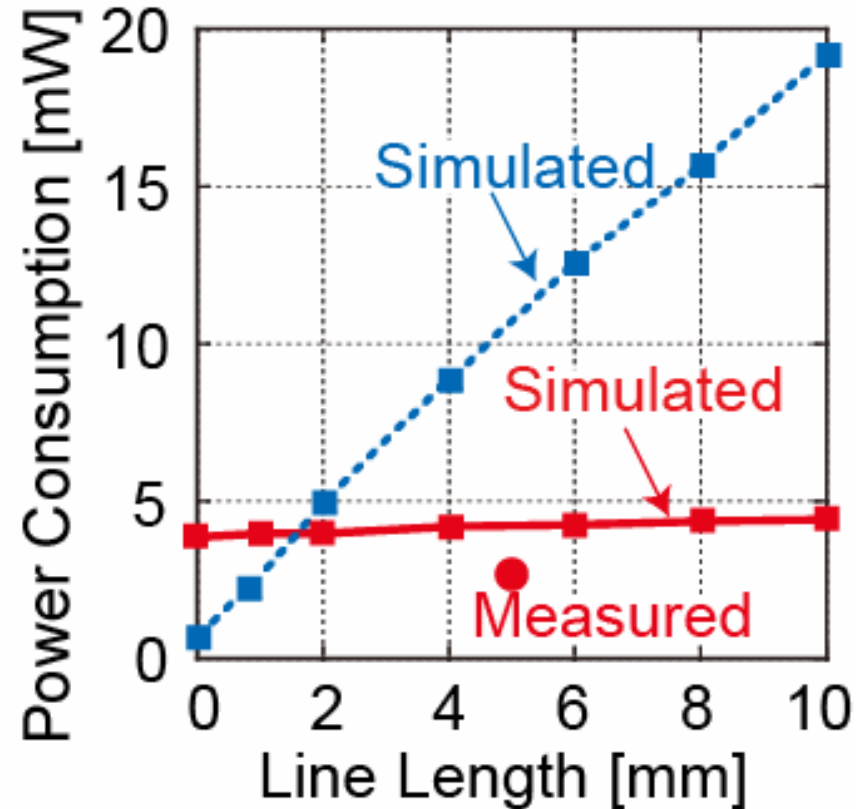
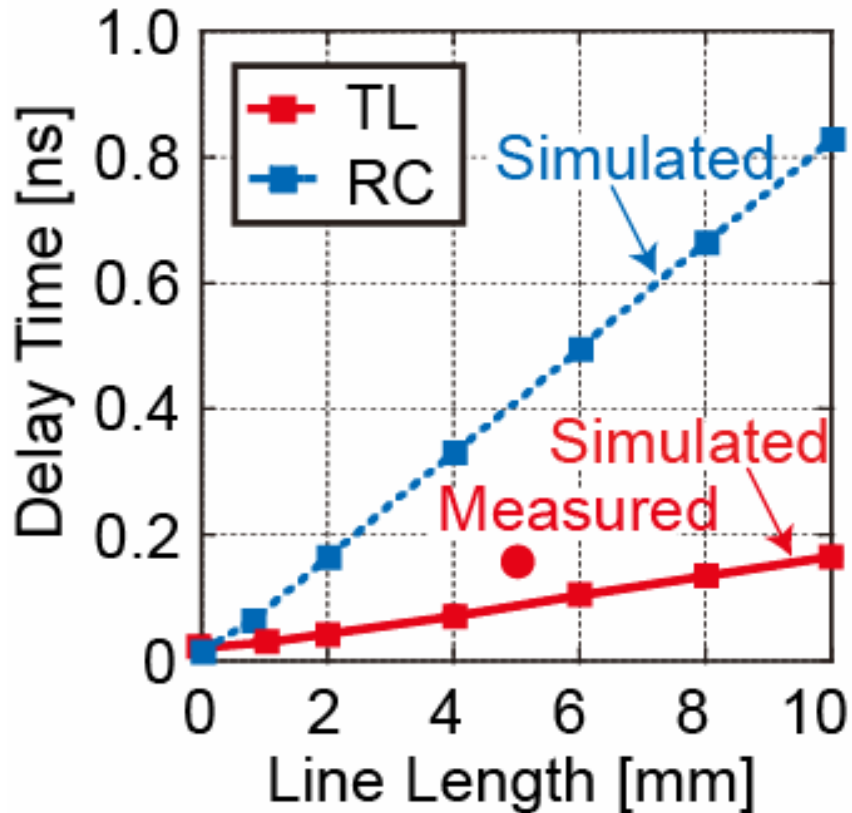
10.5 Gbps

15.9 mV / div  
15.9 ps / div

Process	90 nm standard Si CMOS
The maximum frequency	10.5 Gbps
Average delay of 23 chips	173 ps / 5 mm
Power consumption ( $V_{DD}=1V$ , 10Gbps)	TX : 1.9 mW, RX : 0.8 mW Total : 2.7 mW
Energy per Bit	0.25 pJ / bit

\* Eye-width margin is assumed to be over 20% of period at BER of  $10^{-12}$ .

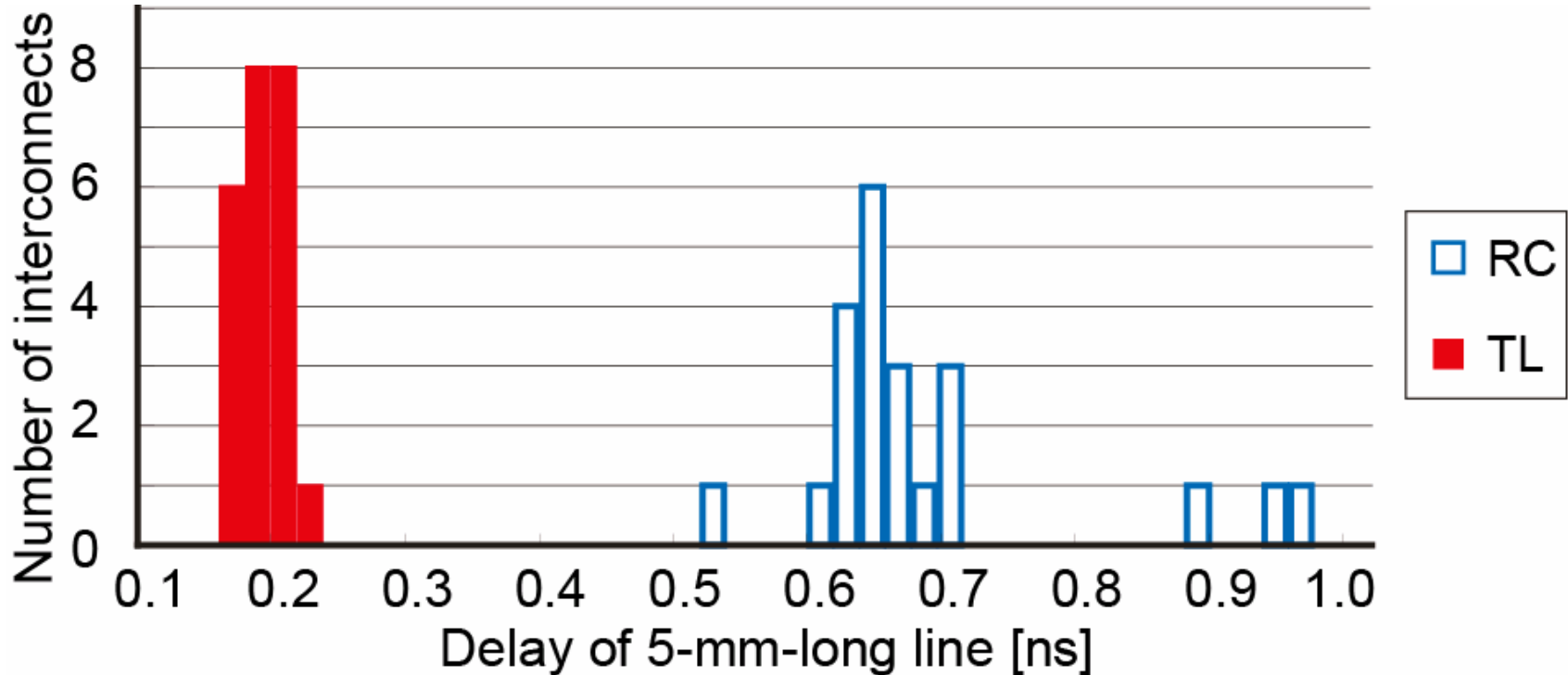
# Comparison of delay and power



- The transmission line interconnect

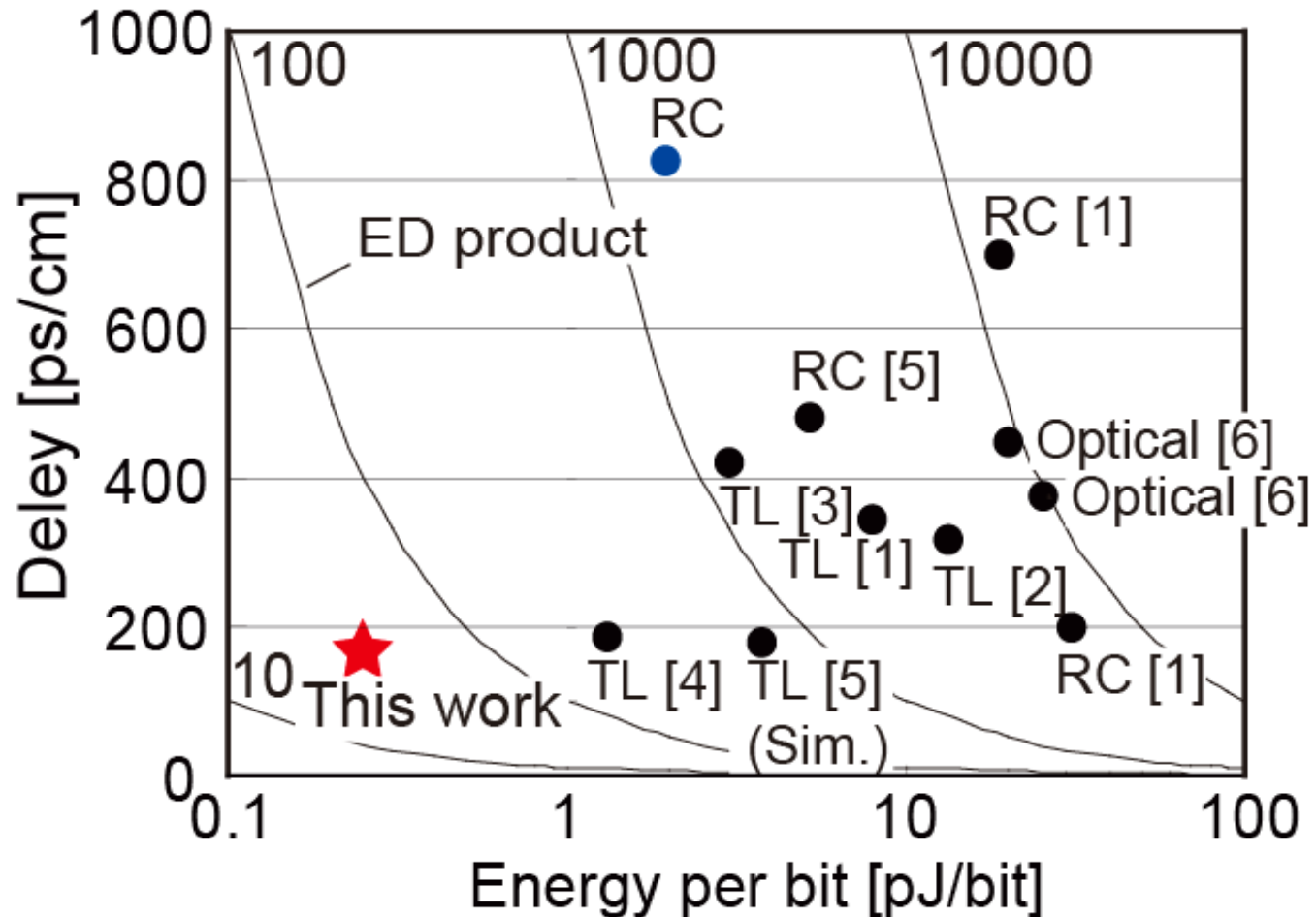
Shorter delay and smaller power consumption than the so-called RC line as the line length increases

RC line: Minimum line widths and optimal repeater spacing (0.4mm)



	TL Interconnect	RC Line
Average delay (23 chip)	173ps	697ps
Delay variation ( $3\sigma$ )	55ps	310ps

# Performance comparison



[1] R. T. Chang, *et al.*, IEEE JSSC, vol. 38, no. 5, pp. 834-838, May 2003.

[2] H. Ito, *et al.*, IEEE A-SSCC, pp. 417-420, 2005.

[3] H. Ito, *et al.*, Circuit Exhibition of ESSCIRC, Poster 26, 2005.

[4] T. Ishii, *et al.*, IEEE A-SSCC, pp. 131-134, 2006.

[5] S. Gomi, *et al.*, IEEE CICC, pp. 325-328, 2004.

[6] E. D. Kyriakis-Bitzaros, *et al.*, JLT, vol. 19, no. 10, pp. 1532-1542, 2001.

- The LVDS-type on-chip transmission line (TL) interconnect was proposed.
- Delay of the proposed TL interconnect is among the shortest, and energy per bit is the best in reported on-chip long interconnects.